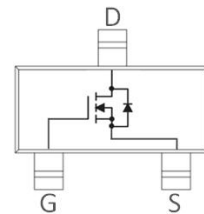


N-Channel MOSFET

Features & Applications

- Trench Power LV MOSFET technology.
- High dense cell design for extremely low RDS(ON).
- Suitable for use as a load switch or in PWM applications.



Marking: A29T

Absolute Maximum Ratings(Ta=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Continuous Drain Current	4	A
I _{DM}	Drain Current-Pulsed	15	A
P _D	Power Dissipation	0.35	W
R _{ΘJA}	Thermal Resistance From Junction To Ambient	350	°C/W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55~+150	°C

Electrical Characteristics (Ta=25°C unless otherwise specified)

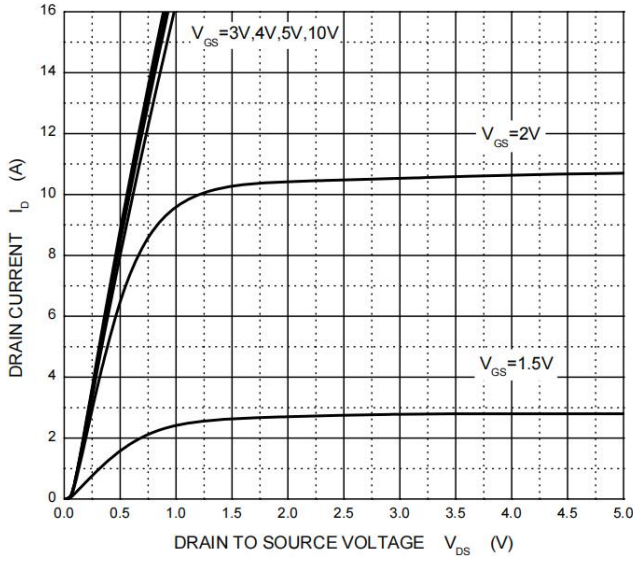
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} =0, I _D =250μA	30			V
V _{GS(th)}	Gate-threshold voltage	V _{DS} =V _{GS} , I _D =250μA	0.6	0.9	1.4	V
I _{GSS}	Collector cut-off current	V _{DS} =0, V _{GS} =±12V			100	nA
I _{DSS}	Collector cut-off current	V _{DS} =30V, V _{GS} =0V			1	μA
R _{DS(on)}	Drain-source on-resistance ^a	V _{GS} =10V, I _D =4A		32	55	mΩ
		V _{GS} =4.5V, I _D =3A		35	70	mΩ
		V _{GS} =2.5V, I _D =2A		50	110	mΩ
g _{FS}	Forward tranconductance ^a	V _{DS} =4.5V, I _D =4A	5			S
V _{SD}	Diode forward voltage	I _S =1A		0.73	0.9	V
Dynamic						
C _{iss}	Input capacitance ^b	V _{DS} =15V, V _{GS} =0V, f=1MHz		390		pF
C _{oss}	Output capacitance ^b			55		
C _{rss}	Reverse transfer capacitance ^b			45		
Switching^b						
t _{d(on)}	Turn-on delay time	V _{GS} =10V, V _{DS} =15V, R _L =3.75Ω, R _{GEN} =6Ω		3.3		nS
t _r	Rise time			1		
t _{d(off)}	Turn-off delay time			22		
t _f	Fall time			2.3		

Notes :

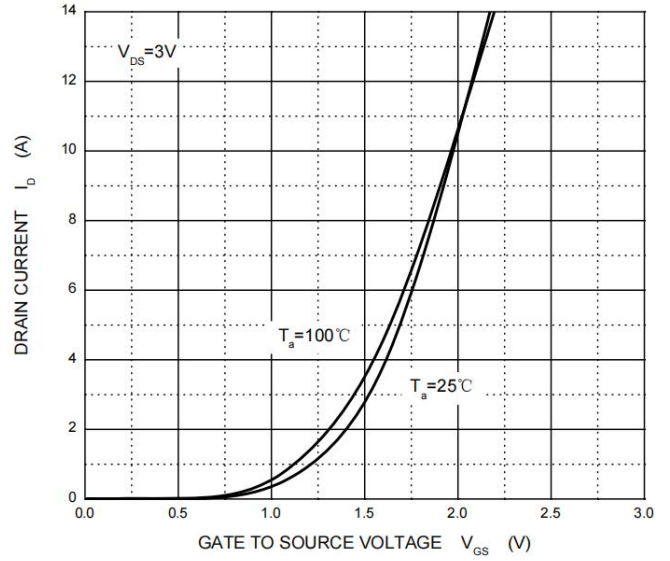
- Pulse Test : Pulse width≤300μs, duty cycle ≤0.5%.
- These parameters have no way to verify.

Typical Characteristics

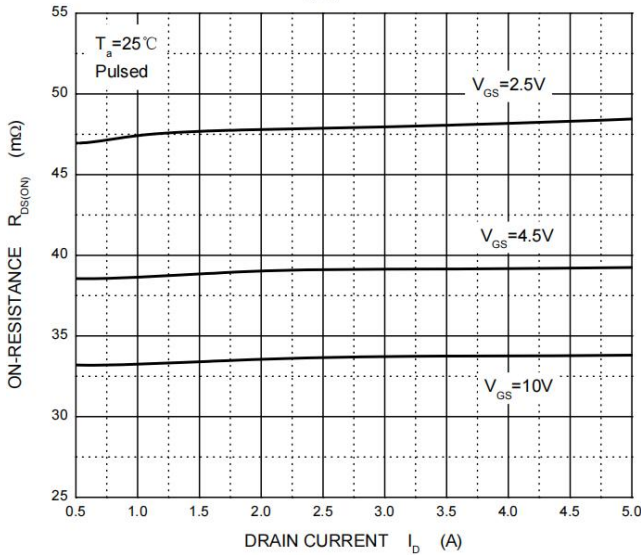
Output Characteristics



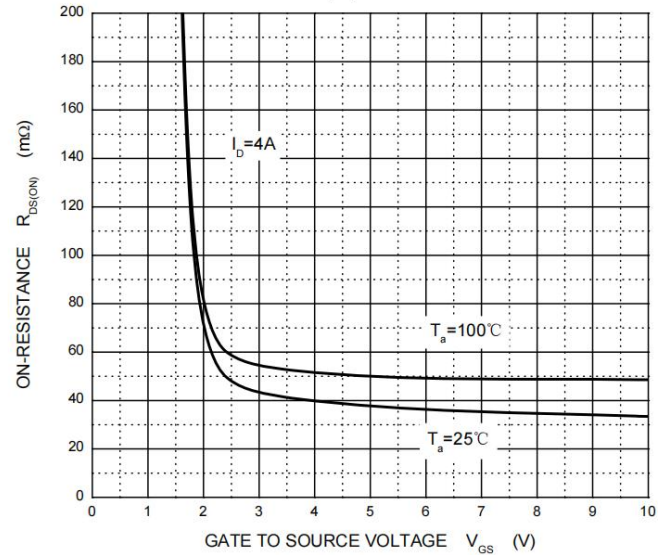
Transfer Characteristics



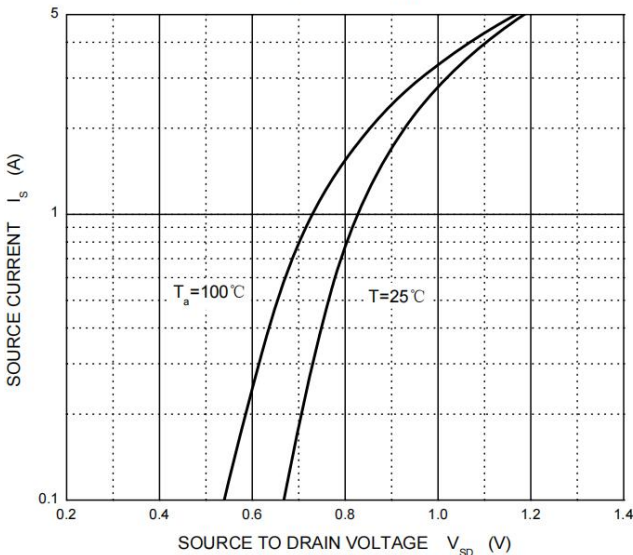
$R_{DS(ON)}$ — I_D



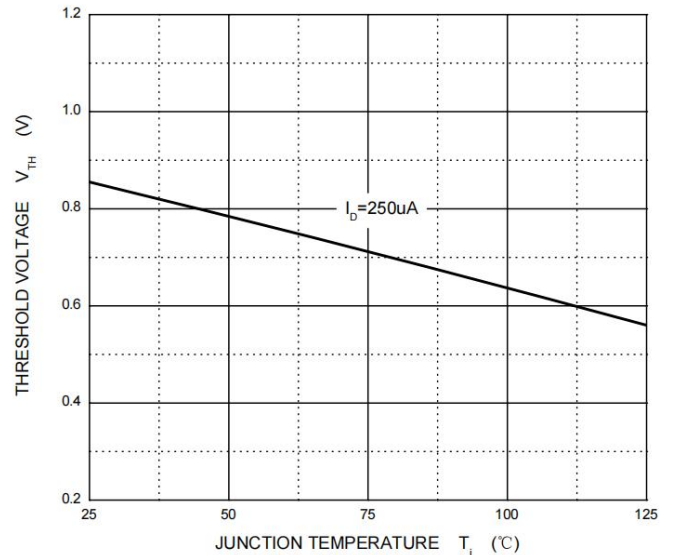
$R_{DS(ON)}$ — V_{GS}



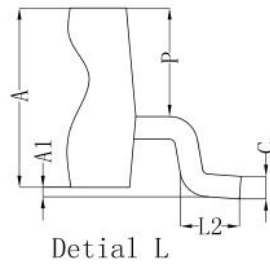
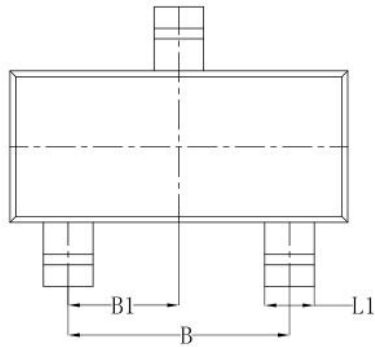
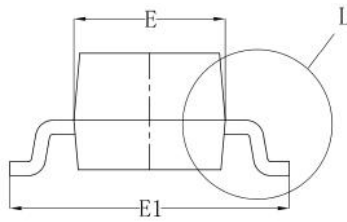
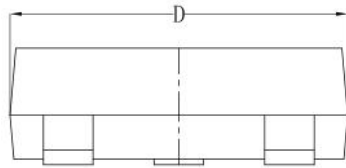
I_S — V_{SD}



Threshold Voltage



SOT-23 Package Outline Dimensions



Symbol	Dim in mm		
	Min	Nom	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
B	1.800	1.900	2.000
B1	0.950 TYP		
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
L1	0.350	0.400	0.500
L2	0.200	0.350	0.450
P	0.550	0.575	0.600